US 20080105932A1

(19) United States

(12) Patent Application Publication

(10) Pub. No.: US 2008/0105932 A1

(43) Pub. Date: May 8, 2008

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(54) PARTIAL FINFET MEMORY CELL

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(21) Appl. No.: **11/588,483**

(22) Filed: **Oct. 27, 2006**

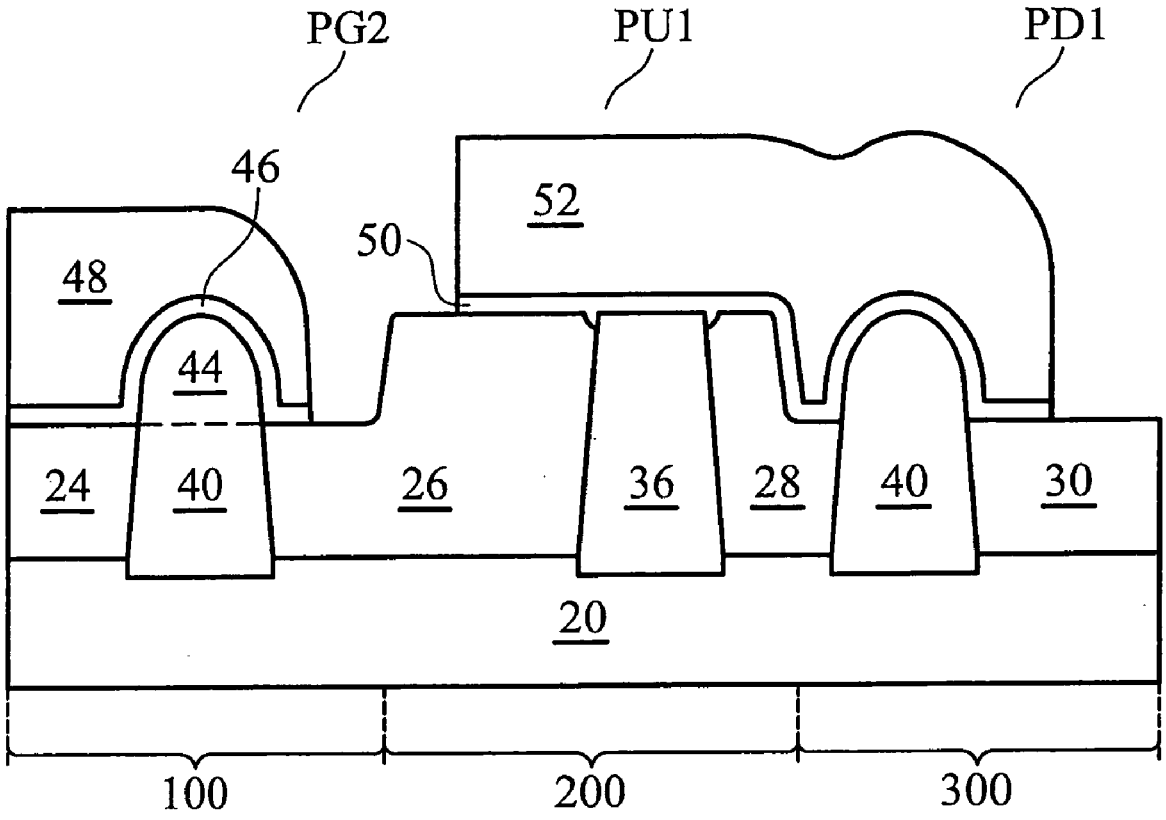
Related U.S. Application Data

(60) Provisional application No. 60/849,047, filed on Oct. 2, 2006.

Publication Classification

(51) **Int. Cl.**
H01L 29/76 (2006.01)
H01L 21/336 (2006.01)

(52) **U.S. Cl.** **257/401**; 438/284; 257/E27.067

(57) **ABSTRACT**

A semiconductor structure includes a semiconductor substrate, a planar PMOS device at a surface of the semiconductor substrate, and an NMOS device at the surface of the semiconductor substrate, wherein the NMOS device is a Fin field effect transistor (FinFET).